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Rohm Semiconductor SP8M2FU6TB

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SP8M2

Transistors

4V Drive Nch+Pch MOSFET **SP8M2**

Structure

Silicon N-channel MOSFET/ Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) Built-in G-S protection diode.
- 3) Small surface mount package (SOP8).

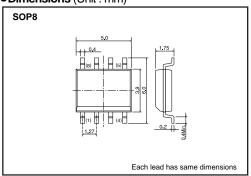
Applications

Switching

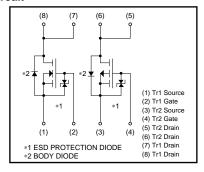
●Package specifications

| | Package | Taping |
|-------|------------------------------|--------|
| Туре | Code | TB |
| | Basic ordering unit (pieces) | 2500 |
| SP8M2 | | 0 |

●Dimensions (Unit:mm)



●Inner circuit



● Absolute maximum ratings (Ta=25°C)

| Parameter | | Symbol | Lin | Unit | |
|-------------------------|------------|--------------------|-------------|------------|-----------|
| | | Symbol | Tr1 : N-ch | Tr2 : P-ch | Offic |
| Drain-source voltage | | VDSS | 30 | -30 | V |
| Gate-source voltage | | V _{GSS} | ±20 | ±20 | V |
| Drain current | Continuous | I _D | ±3.5 | ±3.5 | А |
| | Pulsed | I_{DP}^{*1} | ±14 | ±14 | Α |
| Source current | Continuous | Is | 1.6 | -1.6 | Α |
| (Body diode) | Pulsed | I _{SP} *1 | 14 | -14 | A |
| Total power dissipation | | P _D *2 | 2.0 | | W / TOTAL |
| Channel temperature | | Tch | 150 | | °C |
| Storage temperature | | Tstg | −55 to +150 | | °C |

^{*1} Pw≤10μs, Duty cycle≤1%

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*2 Mounted on a ceramic board.



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Datasheet of SP8M2FU6TB - MOSFET N/P-CH 30V 3.5A 8SOIC

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Transistors

N-ch

●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|------------------------|------|------|------|------|---|
| Gate-source leakage | Igss | _ | _ | ±10 | μΑ | V _{GS} =±20V, V _{DS} =0V |
| Drain-source breakdown voltage | V _(BR) DSS | 30 | - | _ | ٧ | I _D = 1mA, V _{GS} =0V |
| Zero gate voltage drain current | IDSS | _ | - | 1 | μА | V _{DS} = 30V, V _{GS} =0V |
| Gate threshold voltage | VGS (th) | 1.0 | - | 2.5 | V | V _{DS} = 10V, I _D = 1mA |
| Otation Indiana and a state | | - | 59 | 83 | mΩ | I _D = 3.5A, V _{GS} = 10V |
| Static drain-source on-state resistance | R _{DS (on)} * | - | 93 | 130 | mΩ | I _D = 3.5A, V _{GS} = 4.5V |
| resistance | | - | 107 | 150 | mΩ | I _D = 3.5A, V _{GS} = 4V |
| Forward transfer admittance | Y _{fs} * | 2.0 | - | _ | S | V _{DS} = 10V, I _D = 3.5A |
| Input capacitance | Ciss | _ | 140 | _ | pF | V _{DS} = 10V |
| Output capacitance | Coss | _ | 45 | _ | pF | V _{GS} =0V |
| Reverse transfer capacitance | Crss | _ | 30 | _ | pF | f=1MHz |
| Turn-on delay time | td (on) * | - | 6 | _ | ns | V _{DD} ≒ 15V |
| Rise time | tr * | - | 6 | _ | ns | ID= 1.75A |
| Turn-off delay time | t _{d (off)} * | - | 17 | _ | ns | Vgs= 10V RL= 8.57Ω |
| Fall time | t _f * | | 4 | _ | ns | R _G =10Ω |
| Total gate charge | Qg * | ı | 2.5 | 3.5 | nC | V _{DD} ≒15V, V _{GS} =5V |
| Gate-source charge | Q _{gs} * | ı | 0.8 | - | nC | I _D = 3.5A |
| Gate-drain charge | Q _{gd} * | _ | 0.8 | _ | nC | $R_L=4.29\Omega$, $R_G=10\Omega$ |

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|--------|------|------|------|------|--|
| Forward voltage | Vsp* | - | _ | 1.2 | V | I _S = 6.4A, V _{GS} =0V |

*Pulsed





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Transistors

P-ch

●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|------------------------|------|------|------|------|--|
| Gate-source leakage | Igss | - | - | ±10 | μΑ | V _{GS} = ±20V, V _{DS} =0V |
| Drain-source breakdown voltage | V _{(BR) DSS} | -30 | - | _ | V | I _D = -1mA, V _{GS} =0V |
| Zero gate voltage drain current | IDSS | 1 | ı | -1 | μΑ | V _{DS} = -30V, V _{GS} =0V |
| Gate threshold voltage | Vgs (th) | -1.0 | ı | -2.5 | V | Vps= -10V, Ip= -1mA |
| Otatia dania annua an atata | | _ | 65 | 90 | mΩ | I _D = -3.5A, V _G S= -10V |
| Static drain-source on-state resistance | R _{DS} (on)* | - | 100 | 140 | mΩ | I _D = -1.75A, V _G s= -4.5V |
| resistance | | - | 120 | 165 | mΩ | I _D = -1.75A, V _G s= -4V |
| Forward transfer admittance | Y _{fs} * | 1.8 | - | _ | S | V _{DS} = -10V, I _D = -1.75A |
| Input capacitance | Ciss | _ | 490 | _ | pF | V _{DS} = -10V |
| Output capacitance | Coss | _ | 110 | _ | pF | V _{GS} = 0V |
| Reverse transfer capacitance | Crss | _ | 75 | _ | pF | f=1MHz |
| Turn-on delay time | td (on) * | 1 | 10 | - | ns | V _{DD} ≒ –15V |
| Rise time | tr * | _ | 15 | _ | ns |] ID= −1.75A VGS= −10V |
| Turn-off delay time | t _{d (off)} * | - | 35 | _ | ns | VGS= -10V RL= 8.57Ω |
| Fall time | t _f * | - | 10 | _ | ns | R _G = 10Ω |
| Total gate charge | Qg * | ı | 5.5 | 7.7 | nC | V _{DD} ≒-15V, V _{GS} =-5V |
| Gate-source charge | Q _{gs} * | ı | 1.5 | - | nC | I _D = -3.5A |
| Gate-drain charge | Q _{gd} * | _ | 2.0 | _ | nC | $R_L=4.29\Omega$, $R_G=10\Omega$ |

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|--------|------|------|------|------|---|
| Forward voltage | Vsp* | _ | _ | -1.2 | V | I _S = -1.6A, V _{GS} =0V |

^{*}Pulsed



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Appendix

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